

MRF229 MRF230

MRF229
CASE 79-03, STYLE 5

MRF230
CASE 79-02, STYLE 1
TO-39 (TO-205AD)

HIGH FREQUENCY TRANSISTOR

NPN SILICON



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	18	Vdc
Collector-Base Voltage	V_{CBO}	36	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	0.5	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ (1) Derate above 25°C	P_D	5.0 28.6	Watts mW/ $^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	$^\circ\text{C/W}$

(1) These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as Class C RF Amplifiers.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 25\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	18	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 25\text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	36	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.25\text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 15\text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	0.5	mAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 250\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	5.0	—	—
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SMALL SIGNAL CHARACTERISTICS

Output Capacitance ($V_{CB} = 12.5\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	—	25	pF
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FUNCTIONAL TEST (FIGURE 1)

Common-Emitter Amplifier Power Gain ($V_{CC} = 12.5\text{ Vdc}$, $P_{out} = 1.5\text{ W}$, $f = 90\text{ MHz}$)	G_{PE}	10	—	dB
Collector Efficiency ($V_{CC} = 12.5\text{ Vdc}$, $P_{out} = 1.5\text{ W}$, $f = 90\text{ MHz}$)	η	55	—	%
Load Mismatch ($V_{CC} = 12.5\text{ Vdc}$, $P_{out} = 1.5\text{ W}$, $f = 90\text{ MHz}$, $T_C \leq 25^\circ\text{C}$)	—	VSWR > 30:1 Through All Phase Angles in 3 Second Interval After Which Devices Will Meet G_{PE} Test Limits		

FIGURE 1 – 90 MHz TEST CIRCUIT SCHEMATIC

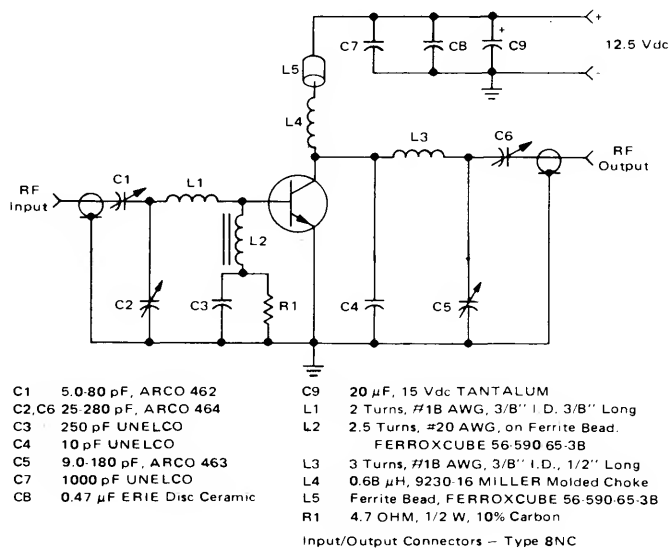


FIGURE 2 – OUTPUT POWER versus INPUT POWER

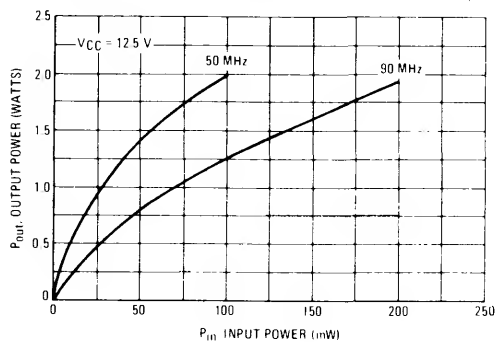


FIGURE 3 – OUTPUT POWER versus FREQUENCY

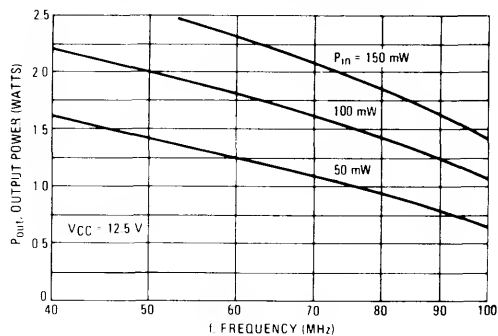


FIGURE 4 – OUTPUT POWER versus SUPPLY VOLTAGE

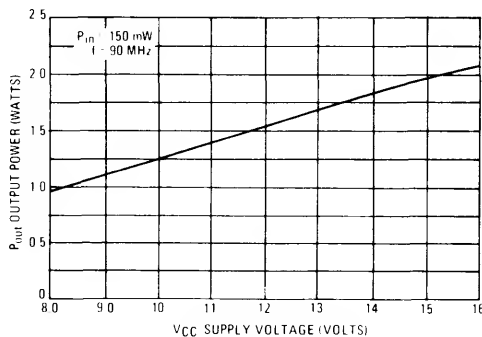


FIGURE 5

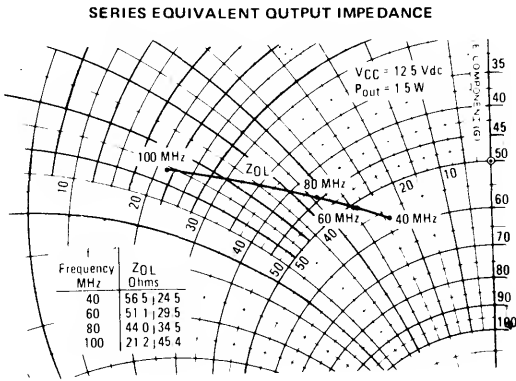
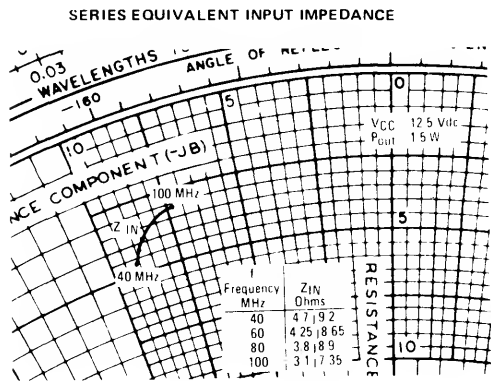


FIGURE 6 – PARALLEL EQUIVALENT INPUT RESISTANCE
versus FREQUENCY

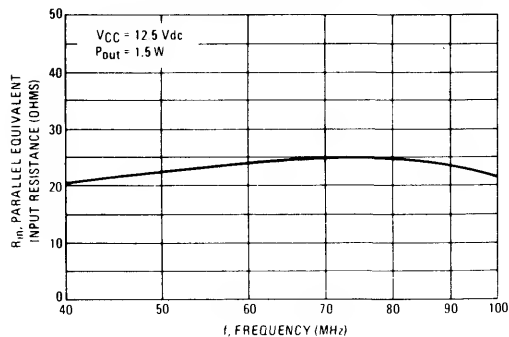


FIGURE 7 – PARALLEL EQUIVALENT INPUT CAPACITANCE
versus FREQUENCY

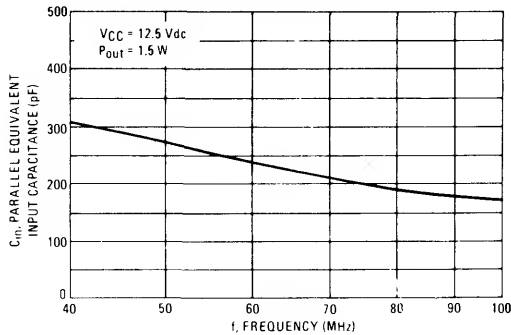


FIGURE 8 – PARALLEL EQUIVALENT OUTPUT RESISTANCE
versus FREQUENCY

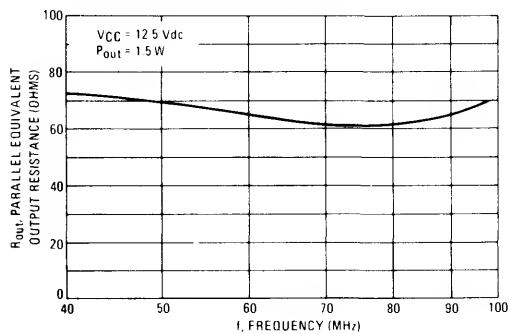


FIGURE 9 – PARALLEL EQUIVALENT OUTPUT CAPACITANCE
versus FREQUENCY

